

Description

The AU3361P0 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time, very low capacitance and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AU3361P0 complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±28kV contact discharge. It is assembled into an ultra-small 0.6×0.3×0.3mm lead-free DFN package. The small size and very low capacitance make AU3361P0 an ideal choice to protect cell phone, digital cameras, audio players, data interface and many other portable applications.

Features

Ultra small package: 0.6x0.3x0.3mm

Protects one data or power line

• Very low capacitance: 3pF typical

Ultra low leakage: nA level

Operating voltage: 3.3V

Low clamping voltage

• 2-pin leadless package

Complies with following standards:

- IEC 61000-4-2 (ESD) immunity test

Air discharge: ±30kV Contact discharge: ±28kV

RoHS compliant

Mechanical Characteristics

Package: DFN0603-2 (0.6×0.3×0.3mm)

• Lead Finish: NiPdAu

Case Material: "Green" Molding Compound.

Terminal Connections: See Diagram Below

Marking Information: See Below

Applications

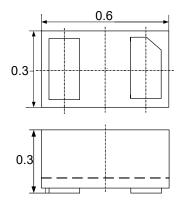
- Cellular Handsets and Accessories
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, USB, LCD Displays

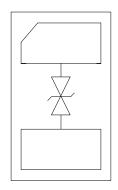
Marking Information

Z3

Z3 = Device Marking Code Dot denotes pin1

Dimensions and Pin Configuration





Package Dimensions (mm) Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size	
AU3361P0	10000/Tape & Reel	7 inch	



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

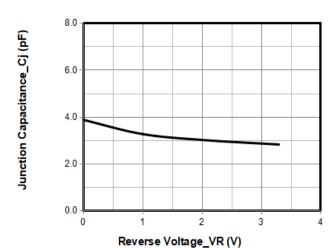
Parameter	Symbol	Value	Unit	
ESD per IEC 61000-4-2 (Air)	VESD	±30	1417	
ESD per IEC 61000-4-2 (Contact)	VESD	±28	kV	
Operating Temperature Range	TJ	-55 to +125	°C	
Storage Temperature Range	Tstg	−55 to +150	°C	

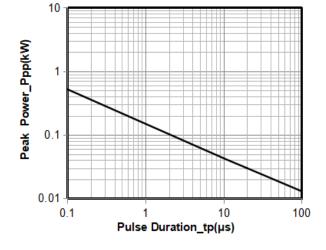
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			3.3	V	Pin 1 to Pin 2 or Pin 2 to Pin 1
Breakdown Voltage	VBR	4.3			V	IT = 1mA, Pin 1 to Pin 2 or Pin 1 to Pin 2
Reverse Leakage Current	I _R			0.2	μA	VRWM = 3.3V, Pin 1 to Pin 2 or Pin 1 to Pin 2
Clamping Voltage	Vc			10	V	IPP = 3A (8 x 20µs pulse), Pin 1 to Pin 2 or Pin 1 to Pin 2
Junction Capacitance	Cl		3		pF	VR = 0V, f = 1MHz

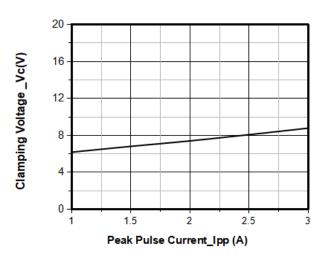


Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

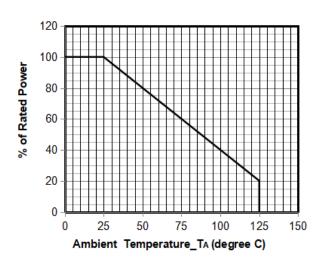




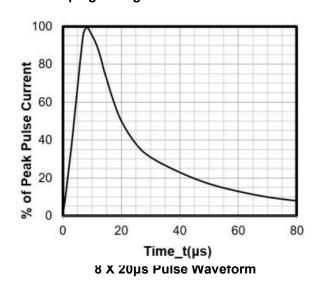
Junction Capacitance vs. Reverse Voltage



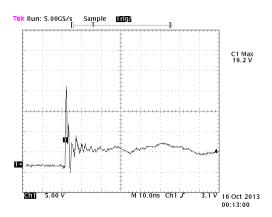
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current



Power Derating Curve

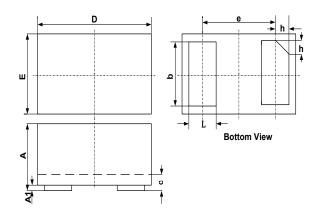


Note: Data is taken with a 10x attenuator
ESD Clamping Voltage

8 kV Contact per IEC61000-4-2

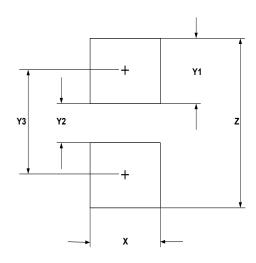


DFN0603-2 Package Outline Drawing



	DIMENSIONS			
	MILLIMETERS			6
SYM	MIN	NOM		MAX
Α	0.230			0.330
A1	0.000	0.020		0.050
b	0.215	0.245		0.275
С	0.120	0.150		0.180
D	0.550	0.600		0.650
е	0.355 BSC			
Е	0.250	0.300		0.350
L	0.160	0.190		0.220
h	0.079 BSC			

Suggested Land Pattern



SYM	DIMENSIONS				
STIVI	MILLIMETERS	INCHES			
Х	0.30	0.012			
Y1	0.25	0.010			
Y2	0.15	0.006			
Y3	0.40	0.016			
Z	0.65	0.026			

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